

2SD1766

Medium Power Transistor

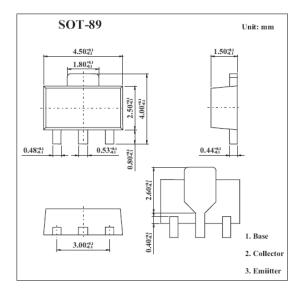
Features

• Low VCE(sat), VCE(sat) = 0.5V (typical)

(Ic = 2A, IB= 0.2A).

hFE Classification

Marking	DB					
Rank	Р	Q	R			
hfe	82~180	120~270	180~390			



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	40	V
Collector-emitter voltage	VCEO	32	V
Emitter-base voltage	Vebo	5	V
Collector current	lc	2	А
	Ic (Pulse) *1	2.5	А
Collector power dissipation	Pc	0.5	W
	Pc *2	2	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

*1. Pw=20ms. *2. 40X40X 0.7mm Ceramic board.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector-base voltage	ВУсво	Ic=50µA	40			V
Collector-emitter voltage	BVCEO	lc=1mA	32			V
Emitter-base voltage	ВVево	Ιε=50μA	5			V
Collector cutoff current	Ісво	Vcb=20V			1	μA
Emitter cutoff current	IEBO	VEB=4V			1	μA
Forward current transfer ratio	hfe	VCE=3V,IC=0.5A	82		390	
Collector-emitter saturation voltage	VCE(sat)	Ic=2A,IB=0.2A		0.5	0.8	V
Transition frequency	f⊤	Vce=5V, Ie= -500mA, f=100MHz		100		MHz
Output capacitance	Cob	Vcb=10V, IE=0A, f=1MHz		30		pF

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